TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

# **TLP127**

Programmable Controllers DC-Output Module Telecommunication

The TOSHIBA mini flat coupler TLP127 is a small outline coupler, suitable for surface mount assembly.

TLP127 consists of a gallium arsenide infrared emitting diode, optically coupled to a darlington photo transistor with an integral base–emitter resistor, and provides 300V VCEO.

- Collector-emitter voltage: 300 V (min.)
- Current transfer ratio: 1000% (min.)
- Isolation voltage: 2500Vrms (min.)
- UL recognized: UL1577, file no. E67349

#### Pin Configurations (top view)



1 : ANODE

- 3 : CATHODE
- 4 : EMITTER 6 : COLLECTOR

## Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	١ <sub>F</sub>	50	mA
LED	Forward current derating	ΔI <sub>F</sub> / °C	–0.7 (Ta ≥ 53°C)	mA / °C
	Pulse forward current	I <sub>FP</sub>	1 (100µs pulse, 100pps)	А
	Reverse voltage	V <sub>R</sub>	5	V
	Junction temperature	Тj	125	°C
	Collector-emitter voltage	V <sub>CEO</sub>	300	V
	Emitter-collector voltage	V <sub>ECO</sub>	0.3	V
for	Collector current	Ι <sub>C</sub>	150	mA
Detector	Collector power dissipation	P <sub>C</sub>	150	mW
	Collector power dissipation derating (Ta $\ge 25^{\circ}$ C)	ΔP <sub>C</sub> /°C	-1.5	mW / °C
	Junction temperature	Тj	125	°C
Storage temperature range		T <sub>stg</sub>	-55~125	°C
Operating temperature range		T <sub>opr</sub>	-55~100	°C
Lead soldering temperature		T <sub>sol</sub>	260 (10s)	°C
Total package power dissipation		PT	200	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP <sub>T</sub> / °C	-2.0	mW / °C
Isolation voltage (Note 1)		BVS	2500 (AC, 1min., R.H.≤ 60%)	Vrms

(Note 1) Device considered a two terminal device: Pins 1, 3 shorted together and pins4, 6 shorted together.

## Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
	Reverse current	I <sub>R</sub>	VR = 5V		_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30		pF
Detector	Collector-emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.1 mA	300	_	_	V
	Emitter-collector breakdown voltage	V <sub>(BR) ECO</sub>	I <sub>E</sub> = 0.1 mA	0.3	_	_	V
	Collector dark current I <sub>CEO</sub>	1	V <sub>CE</sub> = 200 V		10	200	nA
		V <sub>CE</sub> = 200 V, Ta = 85°C	-	_	20	μA	
	Capacitance collector to emitter	C <sub>CE</sub>	V = 0, f = 1 MHz		12	_	pF

#### **Coupled Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Current transfer ratio	I <sub>C</sub> / I <sub>F</sub>	I <sub>F</sub> = 1mA, V <sub>CE</sub> = 1 V	1000	4000	_	%
Saturated CTR	I <sub>C</sub> / I <sub>F (sat)</sub>	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 1 V	500	—	—	%
Collector–emitter saturation voltage		I <sub>C</sub> = 10 mA, I <sub>F</sub> = 1 mA	—	—	1.0	V
	V <sub>CE (sat)</sub>	I <sub>C</sub> = 100 mA, I <sub>F</sub> = 10 mA	0.3	_	1.2	v

#### Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	C <sub>S</sub>	V <sub>S</sub> = 0, f = 1 MHz		0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H.≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
		AC, 1 minute	2500	-	_	V
Isolation voltage	BVS	AC, 1 second, in oil	—	5000	_	V <sub>rms</sub>
		DC, 1 minute, in oil	—	5000	—	V <sub>dc</sub>

#### Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t <sub>r</sub>		_	40	_	μs
Fall time	t <sub>f</sub>	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 10 mA	-	15	_	
Turn–on time	t <sub>on</sub>	R <sub>L</sub> = 100 Ω		50	—	
Turn–off time	t <sub>off</sub>		_	15	—	
Turn–on time	t <sub>ON</sub>		_	5	—	
Storage time	ts	$R_L$ = 180 Ω (Fig.1) V <sub>CC</sub> = 10 V, I <sub>F</sub> = 16 mA	_	40	—	μs
Turn-off time	tOFF		_	80	_	

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>	_	_	200	V
Forward current	١ <sub>F</sub>	_	16	25	mA
Collector current	IC	_	_	120	mA
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

Fig. 1 Switching time test circuit















IFP – VFP 1000 (mA) 500 300 님 100 Pulse forward current 50 30 10 Pulse width ≤ 10µs 5 Repetitive 3 Frequency = 100Hz Ta = 25°C 1 0.6 2.6 3.0 1.8 2.2 1.0 1.4 Pulse forward voltage V<sub>FP</sub> (V)





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